

# RT2N14M

COMPOSITE TRANSISTOR WITH RESISTOR  
FOR SWITCHING APPLICATION  
SILICON NPN EPITAXIAL TYPE

## DESCRIPTION

RT2N14M is a composite transistor with built-in bias resistor

## FEATURE

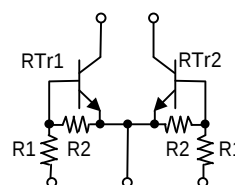
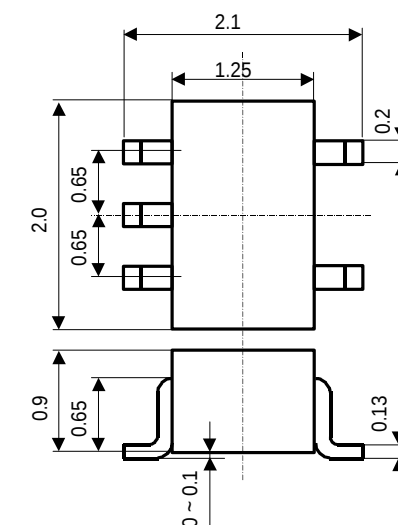
- Built-in bias resistor ( R1=10K $\Omega$  , R2=47K $\Omega$  )
- Mini package for easy mounting

## APPLICATION

Inverted circuit , switching circuit , interface circuit , driver circuit

## OUTLINE DRAWING

Unit:mm



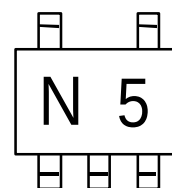
TERMINAL CONNECTOR  
: BASE1  
: EMITTER ( COMMON )  
: BASE2  
: COLLECTOR2  
: COLLECTOR1

JEITA : SC-88A

## MAXIMUM RATINGS (Ta=25 $^{\circ}$ C)(RTr1, RTr2)

| Symbol           | Parameter                                        | Ratings     | Unit |
|------------------|--------------------------------------------------|-------------|------|
| V <sub>CBO</sub> | Collector to Base voltage                        | 50          | V    |
| V <sub>EBO</sub> | Emitter to Base voltage                          | 6           | V    |
| V <sub>CEO</sub> | Collector to Emitter voltage                     | 50          | V    |
| I <sub>C</sub>   | Collector current                                | 100         | mA   |
| I <sub>CM</sub>  | Peak Collector current                           | 200         | mA   |
| P <sub>C</sub>   | Collector dissipation (Total Ta=25 $^{\circ}$ C) | 150         | mW   |
| T <sub>j</sub>   | Junction temperature                             | + 150       |      |
| T <sub>stg</sub> | Storage temperature                              | -55 ~ + 150 |      |

## MARKING



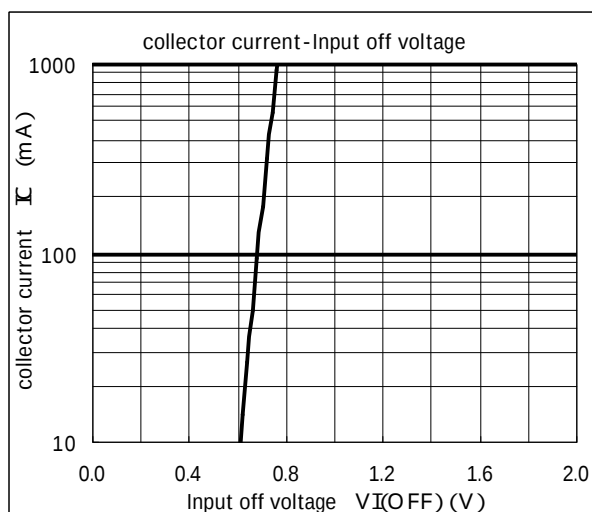
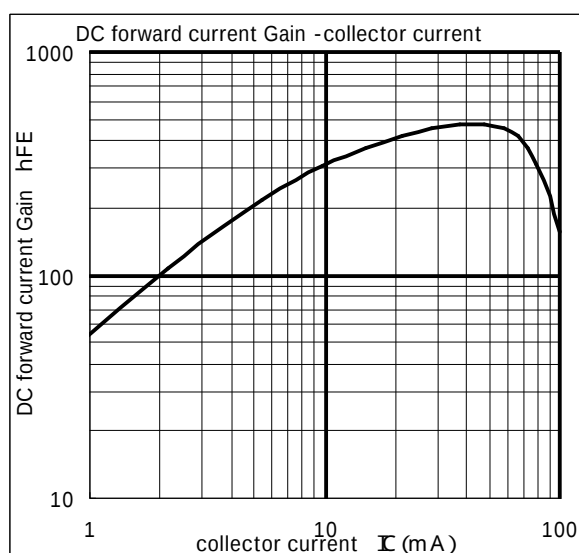
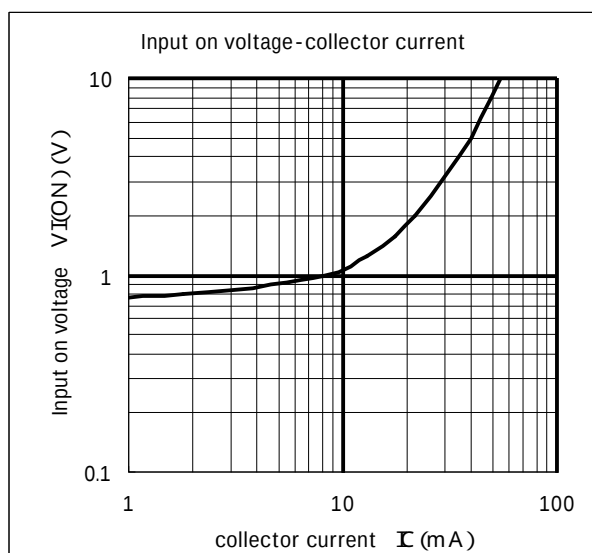
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## ELECTRICAL CHARACTERISTICS (Ta=25 °C)(RT1, RT2)

| Symbol        | Parameter                               | Test conditions               | Limits |     |     | Unit       |
|---------------|-----------------------------------------|-------------------------------|--------|-----|-----|------------|
|               |                                         |                               | Min    | Typ | Max |            |
| $V_{(BR)CBO}$ | Collector to Emitter break down voltage | $I_C=100\mu A, R_{BE}=\infty$ | 50     | -   | -   | V          |
| $I_{CBO}$     | Collector cut off current               | $V_{CB}=50V, I_E=0$           | -      | -   | 0.1 | $\mu A$    |
| $h_{FE}$      | DC forward current gain                 | $V_{CE}=5V, I_C=5mA$          | 50     | -   | -   | -          |
| $V_{CE(sat)}$ | Collector to Emitter saturation voltage | $I_C=10mA, I_B=0.5mA$         | -      | 0.1 | 0.3 | V          |
| $V_{I(ON)}$   | Input on voltage                        | $V_{CE}=0.2V, I_C=5mA$        | -      | 1.0 | 1.8 | V          |
| $V_{I(OFF)}$  | Input off voltage                       | $V_{CE}=5V, I_C=100\mu A$     | 0.4    | 0.7 | -   | V          |
| $R_1$         | Input resistor                          |                               | 7      | 10  | 13  | K $\Omega$ |
| $R_2/R_1$     | Resistor ratio                          |                               | 4.2    | 4.7 | 5.1 | -          |
| $f_T$         | Gain band width product                 | $V_{CE}=6V, I_E=-10mA$        |        | 200 |     | MHz        |

## TYPICAL Characteristics (Tr1, Tr2)





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